

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-5. (Canceled)

6. (Currently Amended) A method of manufacturing a light emitting device, said method comprising:

- forming at least a transparent protrusion;
- forming a pixel electrode to overlap the transparent protrusion;
- forming ~~an organic~~ a light emitting layer to overlap the pixel electrode; and
- forming a cathode over the ~~organic~~ light emitting layer.

7. (Currently Amended) A personal computer comprising a main body, a casing, a display portion, and a keyboard, said personal computer ~~including~~ using a light emitting device: wherein said light emitting device comprises:

- at least a transparent protrusion;
- a pixel electrode over the transparent protrusion;
- ~~an organic~~ a light emitting layer over the pixel electrode; and
- a cathode over the ~~organic~~ light emitting layer,

wherein a surface of the cathode in contact with the ~~organic~~ light emitting layer is uneven.

8. (Original) A personal computer according to claim 7, further comprising:  
an insulating film in transverse direction of the transparent protrusion,  
wherein the insulating film has a high light absorption property.

9. (Original) A personal computer according to claim 7,  
wherein the transparent protrusion is a microlens.

10. (Currently Amended) A portable telephone comprising a main body, a sound output portion, a sound input portion, a display portion, operation switches, and an antenna, said portable telephone ~~including~~ using a light emitting device:

wherein said light emitting device comprises:

at least a transparent protrusion;

a pixel electrode over the transparent protrusion;

~~an organic~~ a light emitting layer over the pixel electrode; and

a cathode over the ~~organic~~ light emitting layer,

wherein a surface of the cathode in contact with the ~~organic~~ light emitting layer is uneven.

11. (Original) A portable telephone according to claim 10, further comprising:  
an insulating film in a transverse direction of the transparent protrusion,  
wherein the insulating film has a high light absorption property.

12. (Original) A portable telephone according to claim 10,  
wherein the transparent protrusion is a microlens.

13. (Original) A portable telephone according to claim 10, further comprising an operation panel, a connecting portion, and a power source switch.

14. (Previously presented) A method according to claim 6, further comprising:  
forming an insulating film in a transverse direction of the transparent protrusion, wherein the insulating film has a high light absorption property.

15. (Currently Amended) A method according to claim 6, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

16. (Currently Amended) A method according to claim 6, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

17. (Currently Amended) A method according to claim 6, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming a first insulating film over the thin film transistor;  
forming a first opening in the first insulating film;  
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;  
forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

18. (Currently Amended) A method according to claim 6, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

19. (Currently Amended) A method according to claim 6, wherein the transparent protrusion ~~includes~~ comprises a microlens.

20. (New) A method according to claim 6, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

21. (New) A method according to claim 6, wherein a surface of the cathode in contact with the light emitting layer is uneven.

22. (New) A personal computer according to claim 7, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

23. (New) A portable telephone according to claim 10, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

24. (New) A method of manufacturing a light emitting device, said method comprising:  
forming at least a protrusion having a property of transmitting light;  
forming a pixel electrode to overlap the protrusion;  
forming a light emitting layer to overlap the pixel electrode; and  
forming a cathode over the light emitting layer.

25. (New) A method according to claim 24, further comprising:  
forming an insulating film in a transverse direction of the protrusion, wherein the insulating film has a high light absorption property.

26. (New) A method according to claim 24, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

27. (New) A method according to claim 24, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

28. (New) A method according to claim 24, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

29. (New) A method according to claim 24, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

30. (New) A method according to claim 24, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

31. (New) A method according to claim 24, wherein a surface of the cathode in contact with the light emitting layer is uneven.

32. (New) A method of manufacturing a light emitting device, said method comprising:  
forming at least a microlens;  
forming a pixel electrode to overlap the microlens;  
forming a light emitting layer to overlap the pixel electrode; and  
forming a cathode over the light emitting layer.

33. (New) A method according to claim 32, further comprising:  
forming an insulating film in a transverse direction of the microlens, wherein the insulating film has a high light absorption property.

34. (New) A method according to claim 32, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

35. (New) A method according to claim 32, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

36. (New) A method according to claim 32, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming a first insulating film over the thin film transistor;  
forming a first opening in the first insulating film;  
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;  
forming a second insulating film in contact with the first insulating film; and  
forming a second opening in the second insulating film.

37. (New) A method according to claim 32, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming a first insulating film over the thin film transistor;  
forming a first opening in the first insulating film;  
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;  
forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and  
forming a second opening in the second insulating film.

38. (New) A method according to claim 32, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

39. (New) A method according to claim 32, wherein a surface of the cathode in contact with the light emitting layer is uneven.



40. (New) A method of manufacturing a light emitting device, said method comprising:  
forming at least a layer containing a transparent material;  
forming a pixel electrode to overlap the layer;  
forming a light emitting layer to overlap the pixel electrode; and  
forming a cathode over the light emitting layer,  
wherein a surface of the cathode in contact with the light emitting layer is uneven.

41. (New) A method according to claim 40, further comprising:  
forming an insulating film in a transverse direction of the layer, wherein the insulating film has a high light absorption property.

42. (New) A method according to claim 40, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

43. (New) A method according to claim 40, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;  
forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

44. (New) A method according to claim 40, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming a first insulating film over the thin film transistor;  
forming a first opening in the first insulating film;  
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;  
forming a second insulating film in contact with the first insulating film; and  
forming a second opening in the second insulating film.

45. (New) A method according to claim 40, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming a first insulating film over the thin film transistor;  
forming a first opening in the first insulating film;  
forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;  
forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and  
forming a second opening in the second insulating film.

46. (New) A method according to claim 40, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

47. (New) A method according to claim 40, wherein the layer has a protrusion.

48. (New) A method of manufacturing a light emitting device, said method comprising:  
forming at least a layer having a property of transmitting light,  
forming a pixel electrode to overlap the layer;  
forming a light emitting layer to overlap the pixel electrode; and  
forming a cathode over the light emitting layer,  
wherein a surface of the cathode in contact with the light emitting layer is uneven.

49. (New) A method according to claim 48, further comprising:  
forming an insulating film in a transverse direction of the layer, wherein the insulating film has a high light absorption property.

50. (New) A method according to claim 48, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor;  
forming a first opening in the insulating film;  
forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and  
forming at least one second opening in the insulating film.

51. (New) A method according to claim 48, further comprising:  
forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;  
forming an insulating film over the thin film transistor, wherein the insulating film has a high light absorption property;  
forming a first opening in the insulating film;

forming a wiring over the insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening; and

forming at least one second opening in the insulating film.

52. (New) A method according to claim 48, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film; and

forming a second opening in the second insulating film.

53. (New) A method according to claim 48, further comprising:

forming a thin film transistor on a substrate, wherein the thin film transistor comprises a semiconductor film and a gate electrode;

forming a first insulating film over the thin film transistor;

forming a first opening in the first insulating film;

forming a wiring over the first insulating film, wherein the wiring is electrically connected to the semiconductor film through the first opening;

forming a second insulating film in contact with the first insulating film, wherein the second insulating film has a high light absorption property; and

forming a second opening in the second insulating film.

54. (New) A method according to claim 48, wherein the light emitting layer comprises at least one of an organic material and an inorganic material.

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55. (New) A method according to claim 48, wherein the layer has a protrusion.

56. (New) A method according to claim 48, wherein the layer contains a transparent material.